## Claims

[c1] 1.A manufacturing method of an active matrix device including a top gate type TFT, which comprises a process of forming the top gate type TFT, wherein the process of forming the top gate type TFT includes the steps of:
forming an oxide film on an inner wall of a CVD processing chamber;
arranging a substrate having source and drain electrodes formed therein in the processing chamber;
doping the source and drain electrodes with P; and
forming an a-Si layer and a gate insulating film in the processing chamber.

[c2] 2.A manufacturing method of an active matrix device according to claim 1, wherein the process of forming the top gate type TFT further comprises the step of removing the oxide film from the inner wall after the step of forming the a-Si layer and the gate insulating film.

[c3] 3.A manufacturing method of an active matrix device according to claim 1, wherein the oxide film contains SiOx.

[c4] 4.A manufacturing method of an active matrix device according to claim 1, wherein the active matrix device is a liquid crystal display.

[c5] 5.A manufacturing method of an active matrix device according to claim 1, wherein the active matrix device is an electroluminescence display.

[c6] 6.A manufacturing method of an active matrix device according to claim 2, wherein the oxide film contains SiOx.

[c7] 7.A manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is a liquid crystal display.

[c8] 8.A manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is a liquid crystal display.

[c9] 9.A manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is an electroluminescence display.

[c10] 10.A manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is an electroluminescence display.

[c11] 11.A manufacturing apparatus for an active matrix device including a top gate type TFT, comprising:
a CVD processing chamber used to manufacture the top gate type TFT, wherein a removable oxide film is formed on an inner wall of the processing chamber for forming the top gate type TFT, and P doping and formation of an a-Si layer and a gate insulating film are carried out in the processing chamber.

[c12] 12.A manufacturing apparatus according to claim 11, wherein the oxide film contains SiOx.

[c13] 13.A manufacturing apparatus according to one of claim 11, wherein the active matrix device is a liquid crystal display.

[c14] 14.A manufacturing apparatus according to one of claim 11, wherein the active matrix device is an electroluminescence display.

[c15] 15.A manufacturing apparatus according to one of claim 12, wherein the active matrix device is a liquid crystal display.

[c16] 16.A manufacturing apparatus according to one of claim 12, wherein the active matrix device is an electroluminescence display.